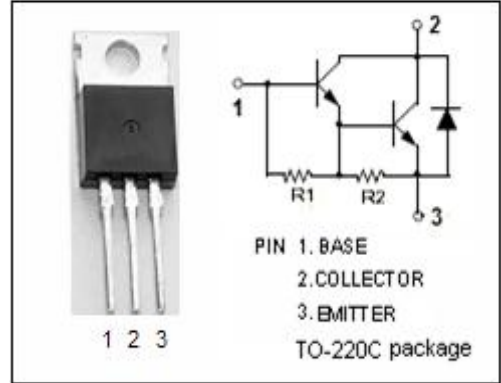


**isc Silicon NPN Darlington Power Transistor**

**2SD1191**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 60V(\text{Min})$
- High DC Current Gain  
:  $h_{FE} = 2000(\text{Min}) @ I_C = 3.5A$
- Low Saturation Voltage
- Complement to Type 2SB881
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

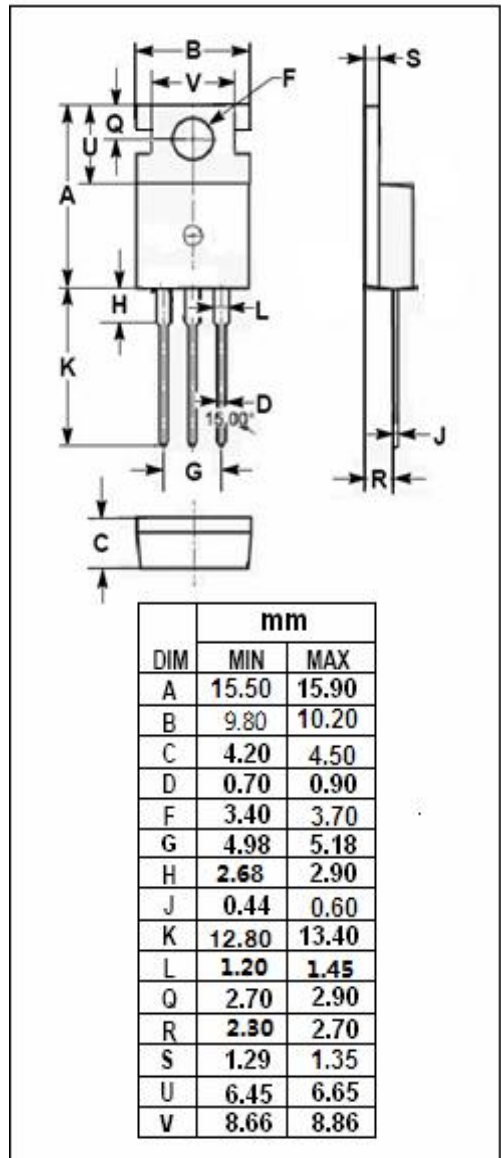


**APPLICATIONS**

- Designed for motor drivers, printer hammer drivers, relay drivers, voltage regulator applications

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	70	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	7	A
$I_{CP}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	1.75	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	30	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



## isc Silicon NPN Darlington Power Transistor

2SD1191

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 3mA; I <sub>E</sub> = 0	70			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 7mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 7mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3.5A; V <sub>CE</sub> = 2V	2000			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 3.5A; V <sub>CE</sub> = 5V		20		MHz
Switching times						
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 3A, I <sub>B1</sub> = I <sub>B2</sub> = 6mA R <sub>L</sub> = 6.7 Ω; V <sub>CC</sub> = 20V; P <sub>W</sub> = 50 μ s; Duty Cycle ≤ 1%		0.6		μ s
t <sub>stg</sub>	Storage Time			3.0		μ s
t <sub>f</sub>	Fall Time			1.7		μ s

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